

SSCE3V382N1

Ultra-low Capacitance Bidirectional Micro Packaged TVS Diodes for ESD Protection

Description

SSCE3V382N1 SSC The is designed with Punch-Through process TVS technology to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium. Also because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed, USB 4.0 super speed, VGA, DVI, HDMI, SDI and other high speed line applications.

It has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by ESD (electrostatic discharge), and EFT (electrical fast transients).

Feature

- ♦ Working voltage: 3.3V
- ♦ Low clamping voltage
- ♦ Low capacitance(0.35pF) for high-speed interfaces
- Low clamping voltage: VCL = 9.0V typ. @ IPP = 16A (TLP)
- ♦ Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test

Air discharge: ±15kV

Contact discharge: ±15kV

- IEC61000-4-5 (Lightning) 3.5A (8/20μs)

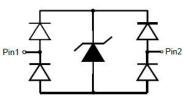
Mechanical data

- ♦ Package: DFN1006-2L(1.0×0.6×0.5mm)
- ♦ Lead finish: 100% matte Sn (Tin)
- ♦ Device meets MSL 3 requirements
- ♦ Case Material: "Green" Molding Compound
- ♦ RoHS Compliant

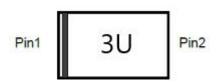
PIN configuration



DFN1006-2L (Bottom View)



Circuit Diagram



<u>Marking</u>

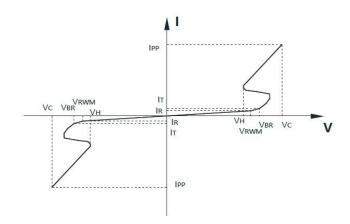
Applications

- High Speed Line: USB1.0/2.0/3.0/4.0,
 VGA, DVI, SDI
- High Definition Multi-Media Interface (HDMI1.3/1.4/2.0)
- ♦ Serial and Parallel Ports
- Notebooks, Desktops, Servers
- Cellular handsets and accessories
- ♦ Portable instrumentation
- ♦ Peripherals



• Electronic Parameter

Symbol	Parameter		
V _{RWM}	Peak Reverse Working Voltage		
I _R	Reverse Leakage Current @ V _{RWM}		
V _{BR}	Breakdown Voltage @ I _T		
I _T	Test Current		
I _{PP}	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
P _{PP}	Peak Pulse Power		
СЈ	Junction Capacitance		



Absolute maximum rating @T_A=25℃

Parameter		Symbol	Value	Unit	
Peak Pulse Power (8/20µs)		P _{PP}	32	W	
Peak Pulse Current (8/20µs)		I _{PP}	3.5	Α	
ESD Rating per IEC61000-4-2:	Contact	V	±15	Is\ /	
	Air	V _{ESD}	±15	kV	
Storage Temperature		T _{STG}	-55/+150	$^{\circ}$	
Operating Temperature		TJ	-55/+125	$^{\circ}$	

• Electrical Characteristics @T_A=25℃

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Peak Reverse Working Voltage	V_{RWM}				3.3	V
Breakdown Voltage	V_{BR}	I _T = 1mA	6.0	8		V
Reverse Leakage Current	I _R	$V_{RWM} = 3.3V$		1	50	nA
Clamping Voltage	Vc	$I_{PP} = 1A, t_P = 8/20 \mu s$		3.6	5.5	V
Clamping Voltage	Vc	$I_{PP} = 3.5A, t_P = 8/20 \mu s$		5.2	7	V
Clamping Voltage ¹⁾	V _{CL}	I_{PP} =16A, t_{P} = 100ns		9		V
Dynamic resistance ¹⁾	RDYN			0.3		Ω
Clamping Voltage ²⁾	V _{CL}	VESD=8KV		9		V
Junction Capacitance	Сл	$V_R = 0V$, $f = 1MHz$		0.35	0.50	pF

Notes:

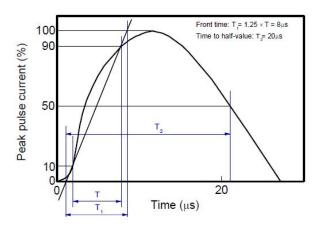
SSC-V1.2

- 1) TLP parameter: $Z0 = 50\Omega$, tp = 100ns, tr = 2ns, averaging window from 60ns to 80ns. RDYN is calculated from 4A to 16A.
- 2) Contact discharge mode, according to IEC61000-4-2.
- 3) Non-repetitive current pulse, according to IEC61000-4-5.

www.sscsemi.com Analog Future



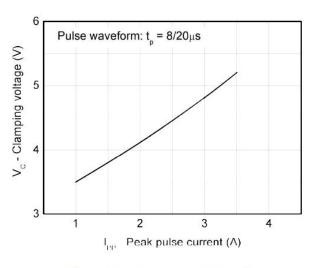
• Typical Performance Characteristics

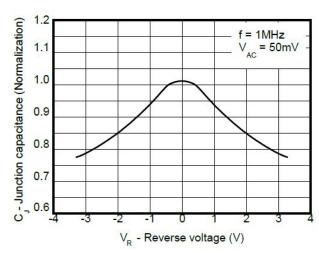


100 90 10 30ns 60ns t

8/20µs Pulse Waveform

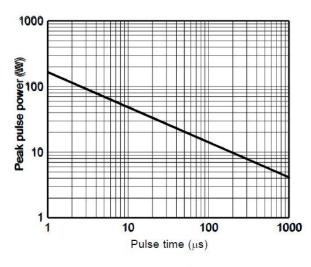


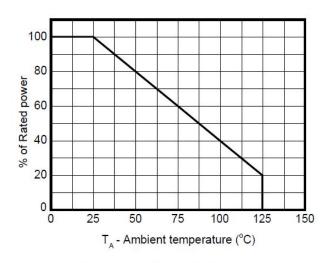




Clamping voltage vs. Peak pulse current

Capacitance vs. Reverse voltage





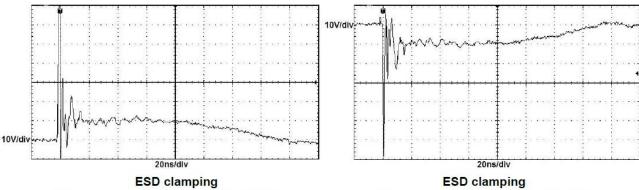
Non-repetitive peak pulse power vs. Pulse time

Power derating vs. Ambient temperature

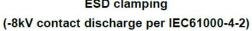
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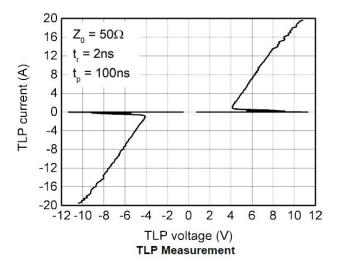


• Typical Performance Characteristics



(+8kV contact discharge per IEC61000-4-2)







• Package Information

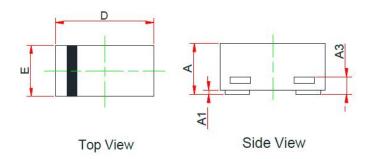
Ordering Information

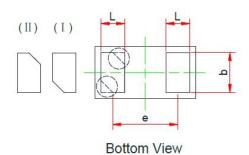
Device	Package	Qty per Reel	Reel Size
SSCE3V382N1	DFN1006-2L	10000	7 Inch

Mechanical Data

Case: DFN1006-2L

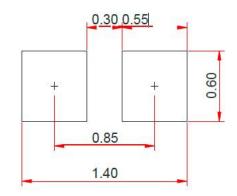
Case Material: Molded Plastic. UL Flammability





DIM	Millimeters				
ואווט	Min	Тур	Max		
Α	0.34	0.45	0.53		
A1	0.00	0.02	0.05		
A3	0.125REF				
D	0.95	1.00	1.08		
Е	0.55	0.60	0.68		
b	0.45	0.5	0.55		
L	0.20	0.25	0.3		
е	0.65BSC				

Recommended Pad outline(Unit: mm)





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